CGH40006P

6 W, RF Power GaN HEMT

Cree's CGH40006P is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT). The CGH40006P, operating from a 28 volt rail, offers a general purpose, broadband solution to a variety of RF and microwave applications. GaN HEMTs offer high efficiency, high gain and wide bandwidth capabilities making the CGH40006P ideal for linear and compressed amplifier circuits. The transistor is available in a solder-down, pill package.

Package Types: 440109
PN's: CGH40006P

FEATURES

- Up to 6 GHz Operation
- 13 dB Small Signal Gain at 2.0 GHz
- 11 dB Small Signal Gain at 6.0 GHz
- 8 W typical at P_{IN} = 32 dBm
- 65 % Efficiency at P_{IN} = 32 dBm
- 28 V Operation

APPLICATIONS

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

RoHS COMPLIANT

Large Signal Models Available for SiC & GaN

PRELIMINARY
Rev 2.1 – April 2012

Absolute Maximum Ratings (not simultaneous) at 25˚C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	84	Volts	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	2.1	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	0.75	A	25˚C
Soldering Temperature[2]	T_S	245	˚C	
Thermal Resistance, Junction to Case[3]	$R_{\theta JC}$	9.5	˚C/W	85˚C
Case Operating Temperature[3]	T_C	-40, +150	˚C	30 seconds

Note:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering at www.cree.com/products/wireless_appnotes.asp
[3] Measured for the CGH40006P at P_{DISS} = 8 W.

Electrical Characteristics (T_C = 25˚C)

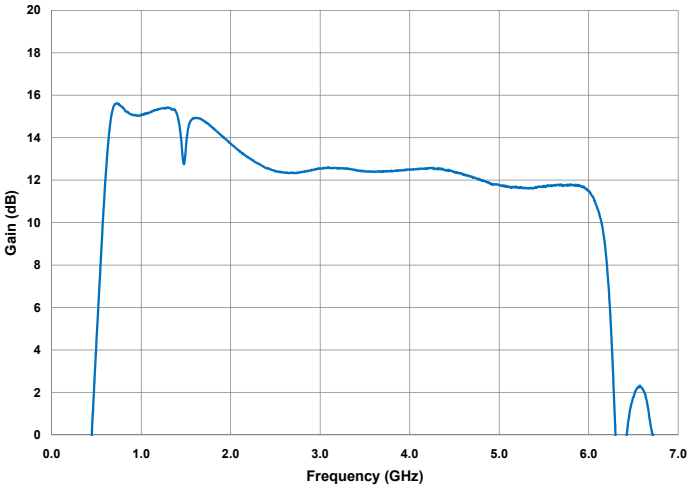
Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 2.1 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DS} = 28 V, I_D = 100 mA
Saturated Drain Current	I_{DS}	1.7	2.1	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	120	–	–	V_{DC}	V_{GS} = -8 V, I_D = 2.1 mA
RF Characteristics[2] (T_C = 25˚C, F_0 = 2.0 GHz unless otherwise noted)						
Small Signal Gain	G_{SS}	11.5	13	–	dB	V_{DD} = 28 V, I_{DQ} = 100 mA
Power Output at P_{IN} = 32 dBm	P_{OUT}	7.0	9	–	W	V_{DD} = 28 V, I_{DQ} = 100 mA
Drain Efficiency[3]	η	53	65	–	%	V_{DD} = 28 V, I_{DQ} = 100 mA, P_{IN} = 32 dBm
Output Mismatch Stress	VSWR	–	–	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 100 mA, P_{IN} = 32 dBm
Dynamic Characteristics						
Input Capacitance	C_{GS}	–	3.0	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Output Capacitance	C_{DS}	–	1.1	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Feedback Capacitance	C_{GD}	–	0.1	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz

Notes:
[1] Measured on wafer prior to packaging.
[2] Measured in CGH40006P-TB.
[3] Drain Efficiency = P_{OUT} / P_{DC}

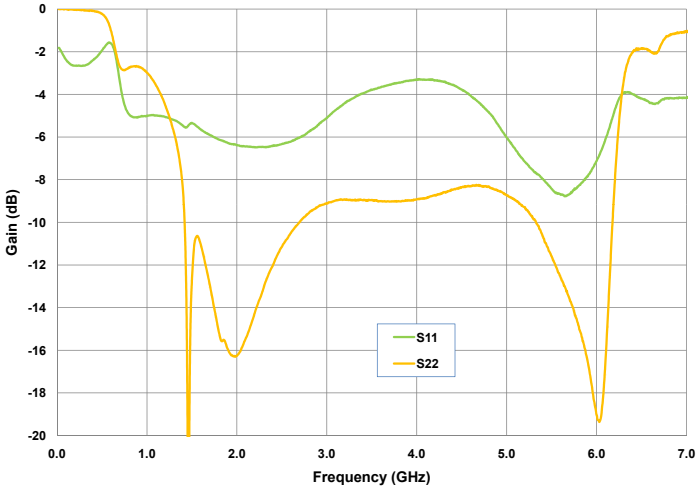
Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Typical Performance

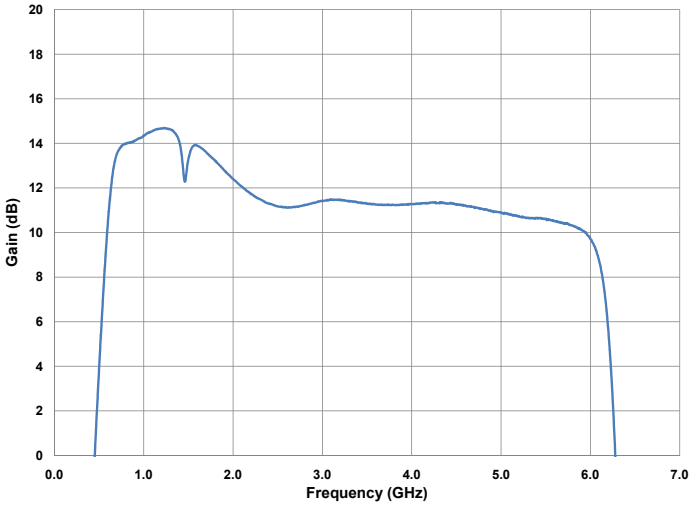
Small Signal Gain vs Frequency at 28 V of the CGH40006P in the CGH40006P-TB



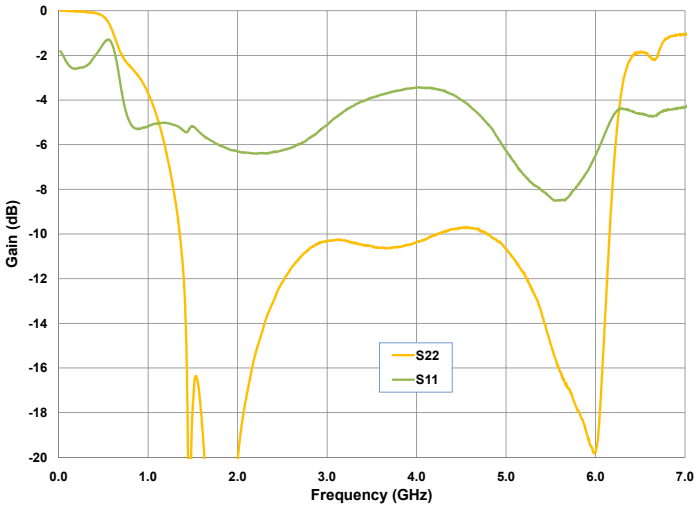
Input & Output Return Losses vs Frequency at 28 V of the CGH40006P in the CGH40006P-TB



Small Signal Gain vs Frequency at 20 V of the CGH40006P in the CGH40006P-TB



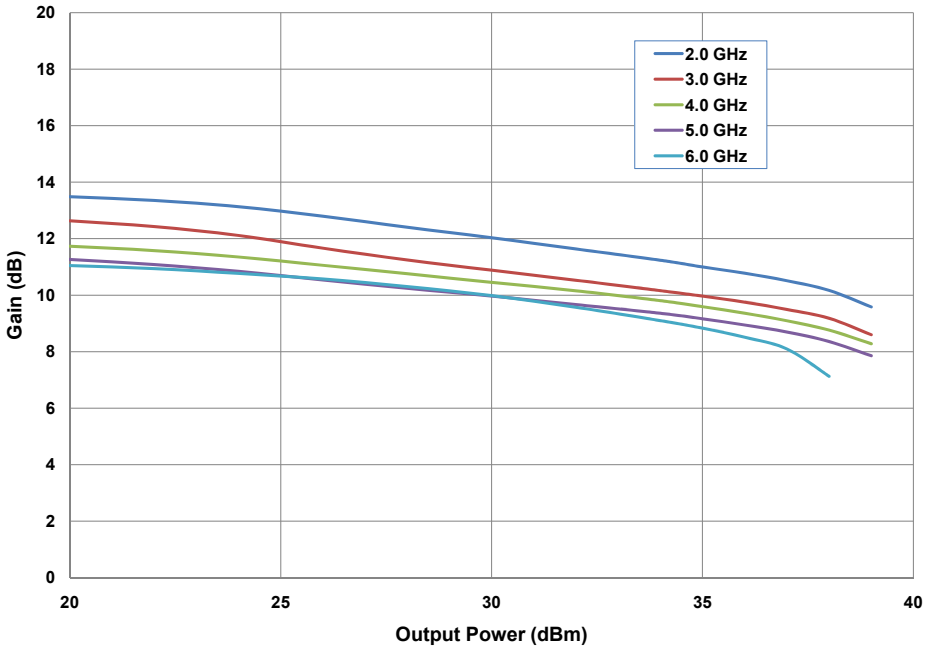
Input & Output Return Losses vs Frequency at 20 V of the CGH40006P in the CGH40006P-TB



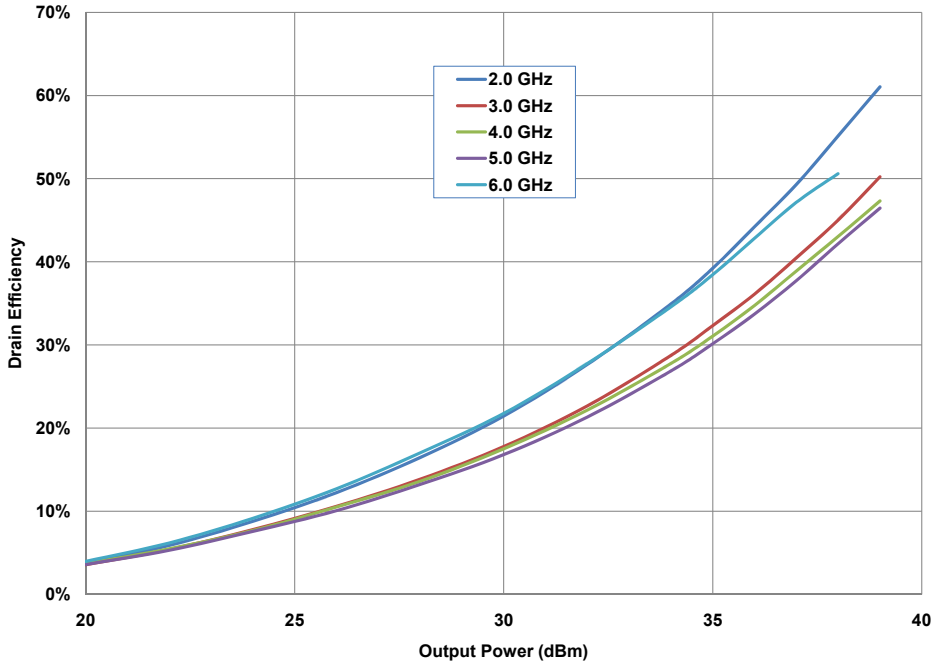
Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Typical Performance

Power Gain vs Output Power as a Function of Frequency of the CGH40006P in the CGH40006P-TB
V_{DD} = 28 V, I_{DQ} = 100 mA



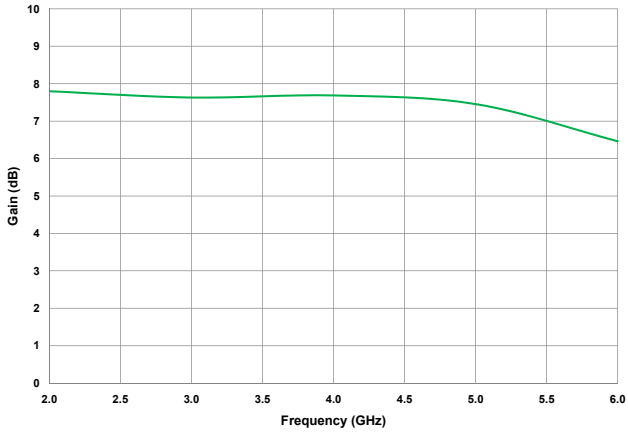
Drain Efficiency vs Output Power as a Function of Frequency of the CGH40006P in the CGH40006P-TB
V_{DD} = 28 V, I_{DQ} = 100 mA



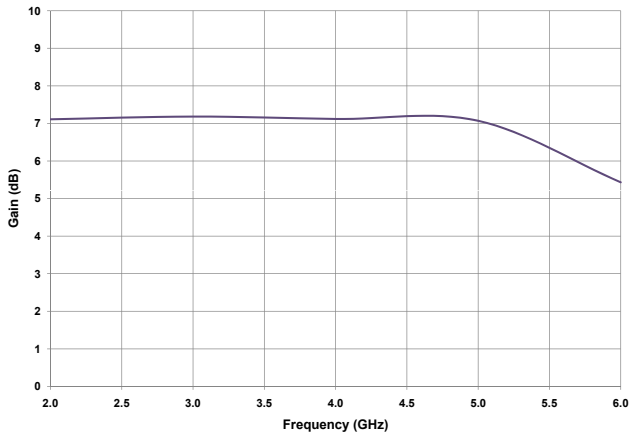
Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Typical Performance

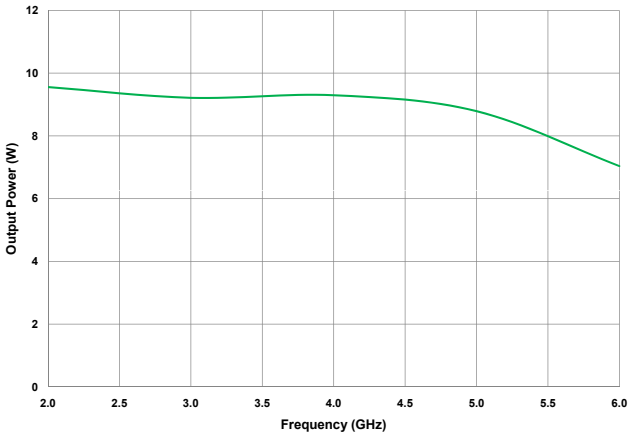
Power Gain vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 32 dBm, V_{DD} = 28 V



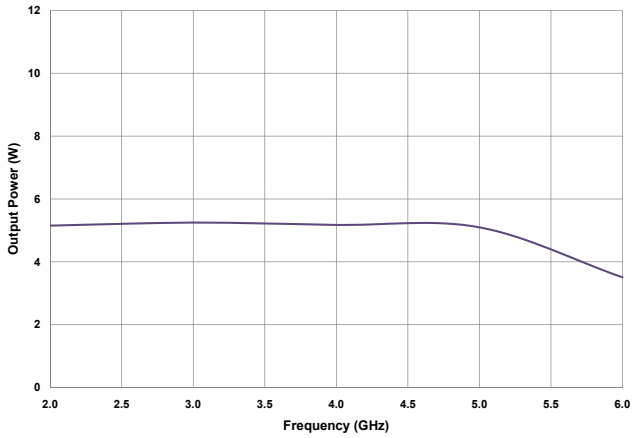
Power Gain vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 30 dBm, V_{DD} = 20 V



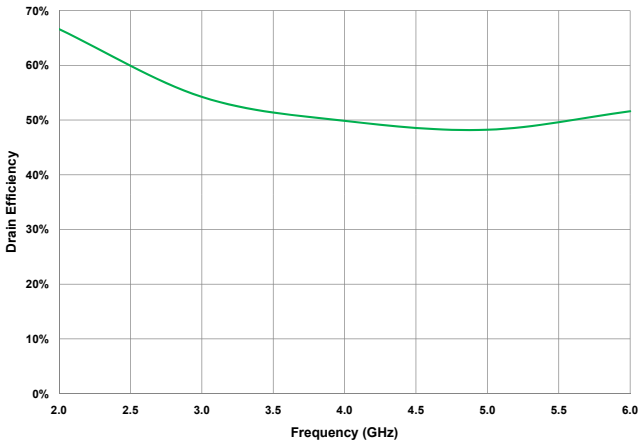
Output Power vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 32 dBm, V_{DD} = 28 V



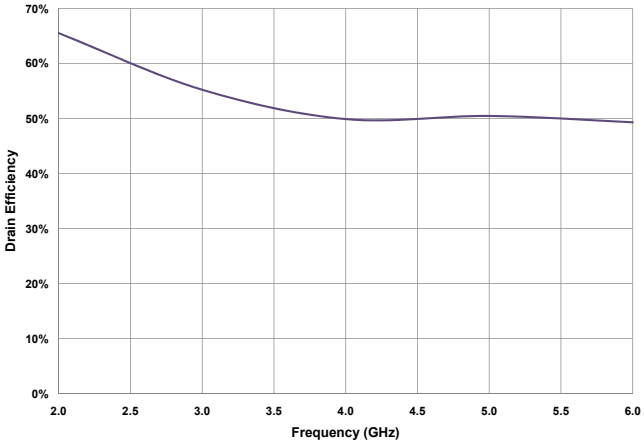
Output Power vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 30 dBm, V_{DD} = 20 V



Drain Efficiency vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 32 dBm, V_{DD} = 28 V



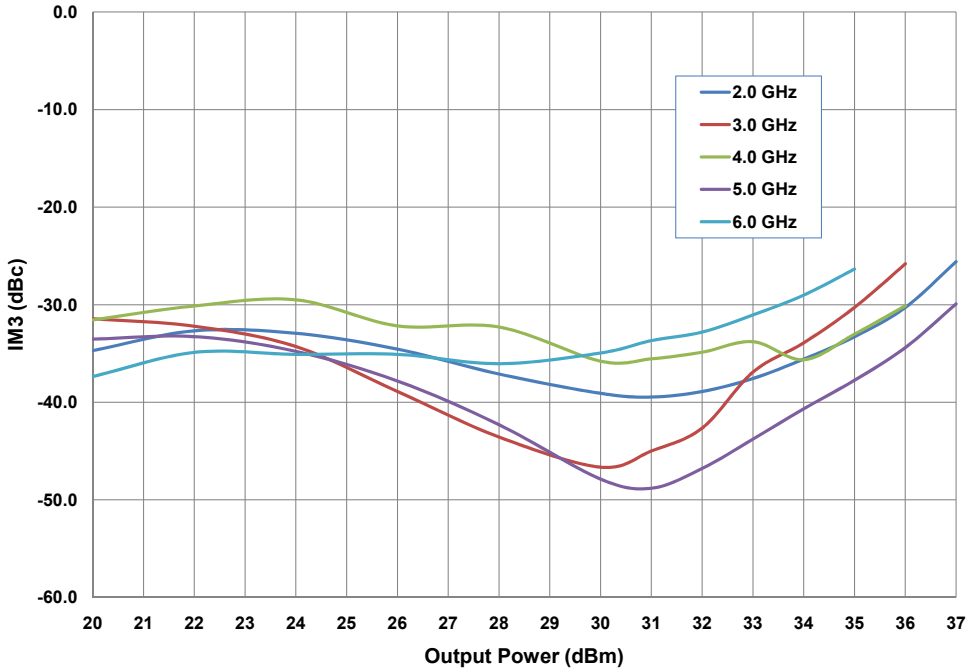
Drain Efficiency vs Frequency of the CGH40006P in the CGH40006P-TB at P_{IN} = 30 dBm, V_{DD} = 20 V



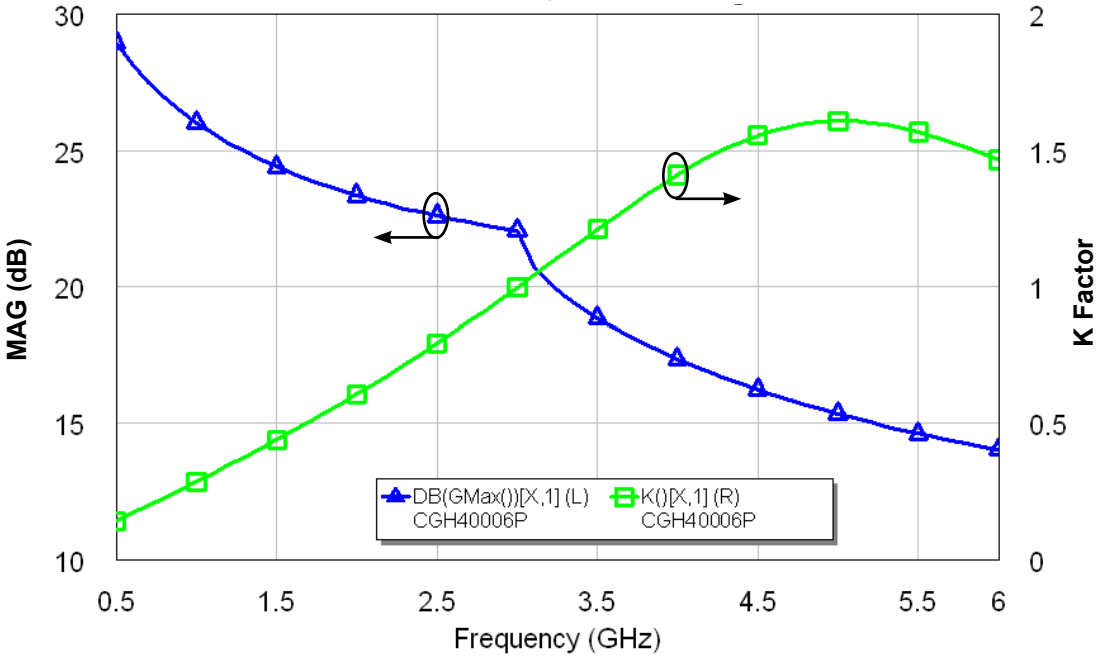
Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Typical Performance

Third Order Intermodulation Distortion vs Average Output Power as a Function of Frequency of the CGH40006P in the CGH40006P-TB
V_{DD} = 28 V, I_{DQ} = 60 mA



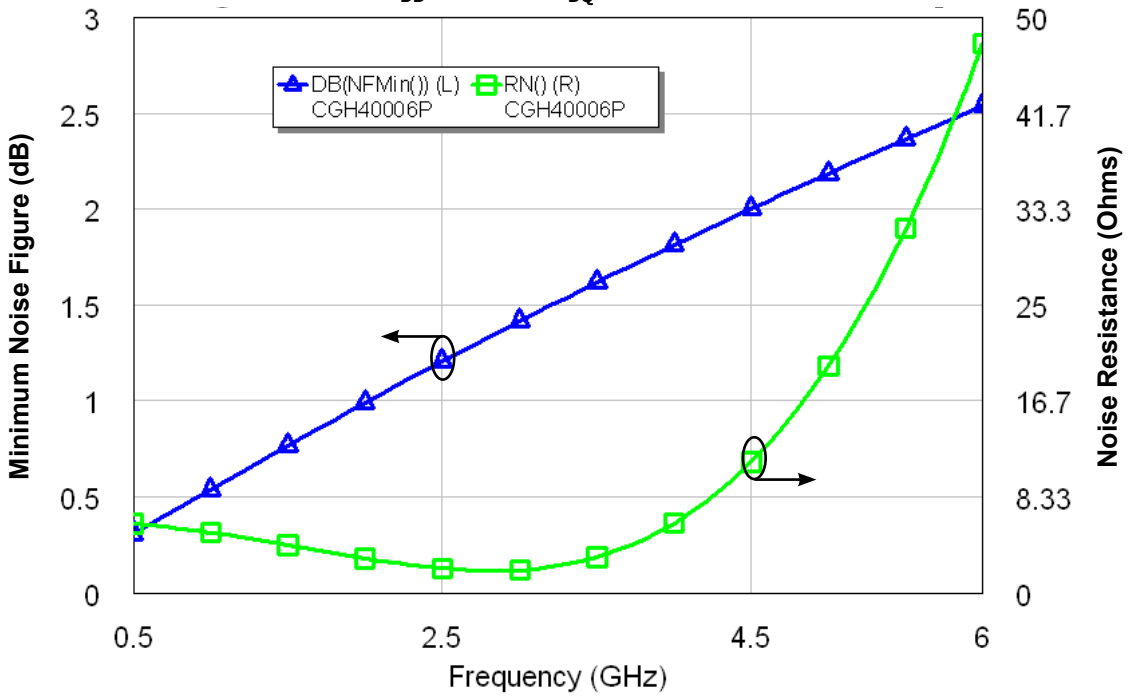
Simulated Maximum Available Gain and K Factor of the CGH40006P
V_{DD} = 28 V, I_{DQ} = 100 mA



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Typical Noise Performance

Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH40006P
V_{DD} = 28 V, I_{DQ} = 100 mA

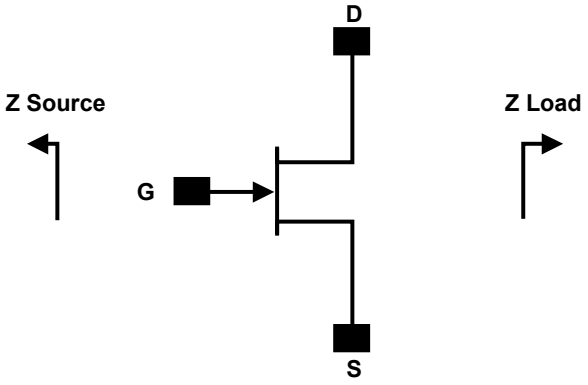


Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A > 250 V	JEDEC JESD22 A114-D
Charge Device Model	CDM	1 < 200 V	JEDEC JESD22 C101-C

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

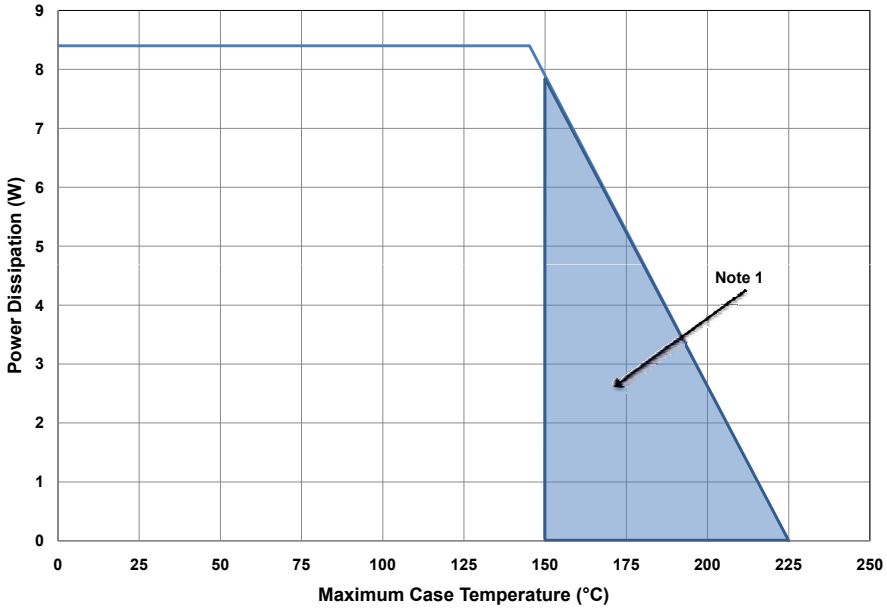
Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
1000	13.78 + j6.9	61.5 + j47.4
2000	4.78 + j1.78	19.4 + j39.9
3000	2.57 - j6.94	12.57 + j23.1
4000	3.54 - j14.86	9.44 + j11.68
5000	4.42 - j25.8	9.78 + j4.85
6000	7.1 - j42.7	9.96 - j4.38

Note 1. V_{DD} = 28V, I_{DQ} = 100mA in the 440109 package.
Note 2. Optimized for power gain, P_{SAT} and PAE.
Note 3. When using this device at low frequency, series resistors should be used to maintain amplifier stability.

CGH40006P Power Dissipation De-rating Curve



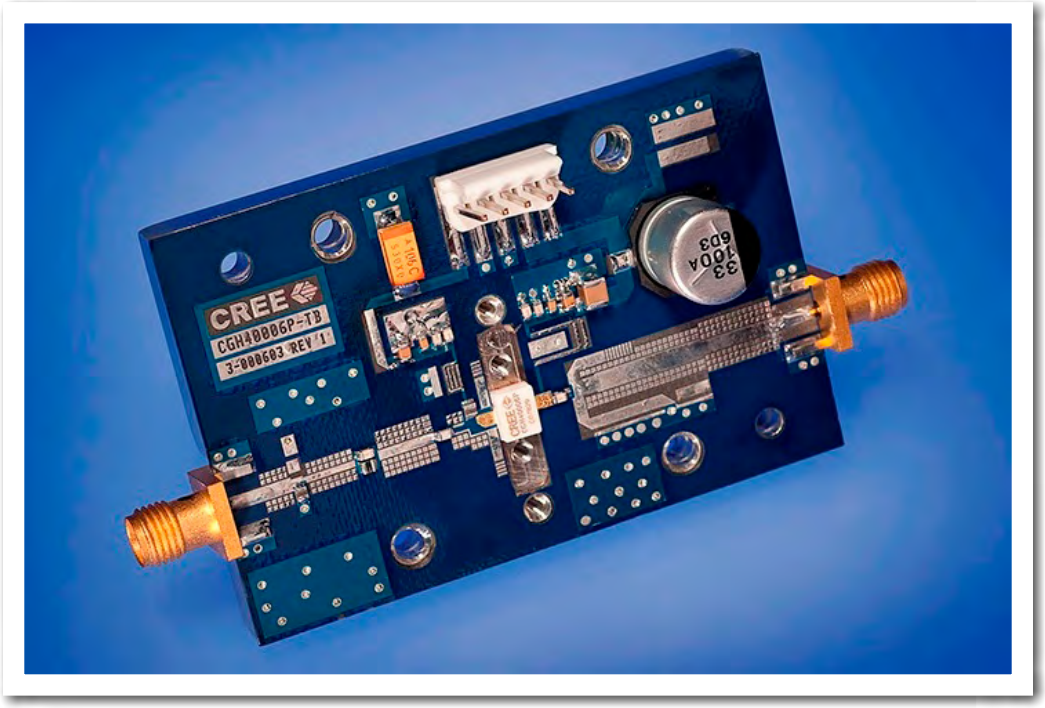
Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

CGH40006P-TB Demonstration Amplifier Circuit Bill of Materials

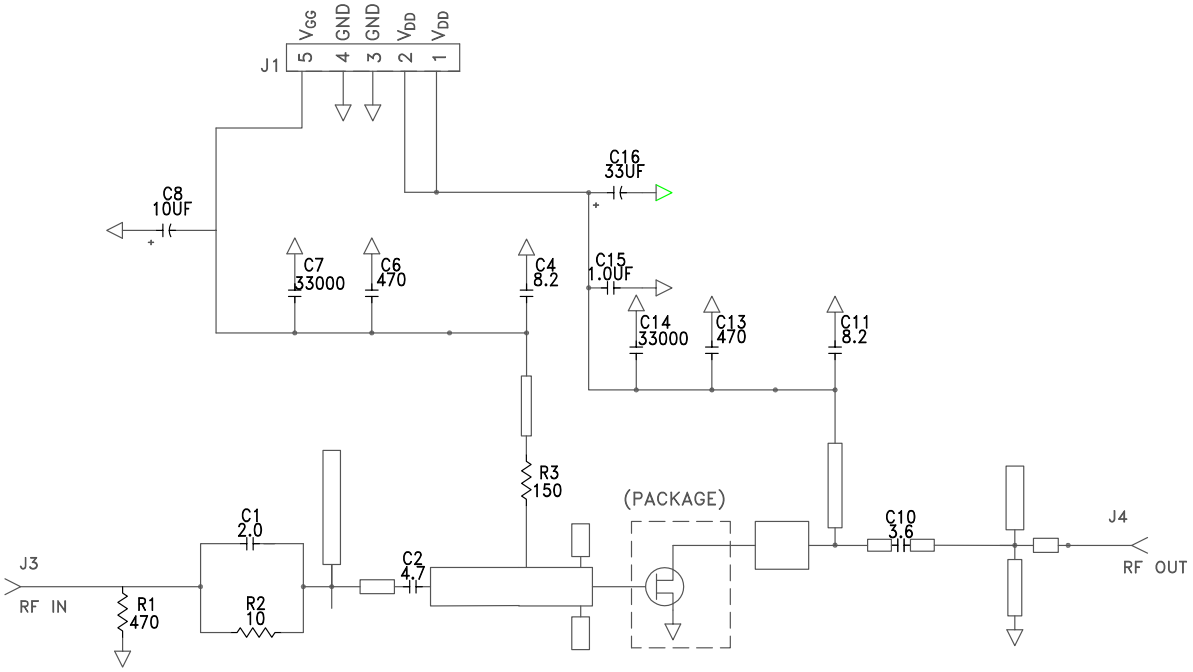
Designator	Description	Qty
R1	RES, AIN, 0505, 470 Ohms (≤5% tolerance)	1
R2	RES, AIN, 0505, 10 Ohms (≤5% tolerance)	1
R3	RES, AIN, 0505, 150 Ohms (≤5% tolerance)	1
C1	CAP, 2.0 pF +/-0.1 pF, 0603, ATC 600S	1
C2	CAP, 4.7 pF +/-0.1 pF, 0603, ATC 600S	1
C10	CAP, 3.6 pF +/-0.1 pF, 0603, ATC 600S	1
C4,C11	CAP, 8.2 pF +/-0.25, 0603, ATC 600S	2
C6,C13	CAP, 470 pF +/-5%, 0603, 100 V	2
C7,C14	CAP, 33000 pF, CER, 100V, X7R, 0805	2
C8	CAP, 10 uf, 16V, SMT, TANTALUM	1
C15	CAP, 1.0 uF +/-10%, CER, 100V, X7R, 1210	1
C16	CAP, 33 uF, 100V, ELECT, FK, SMD	1
J3,J4	CONN, SMA, STR, PANEL, JACK, RECP	2
J1	HEADER RT>PLZ .1CEN LK 5POS	1
-	PCB, RO5880, 20 MIL	1
Q1	CGH40006P	1

CGH40006P-TB Demonstration Amplifier Circuit

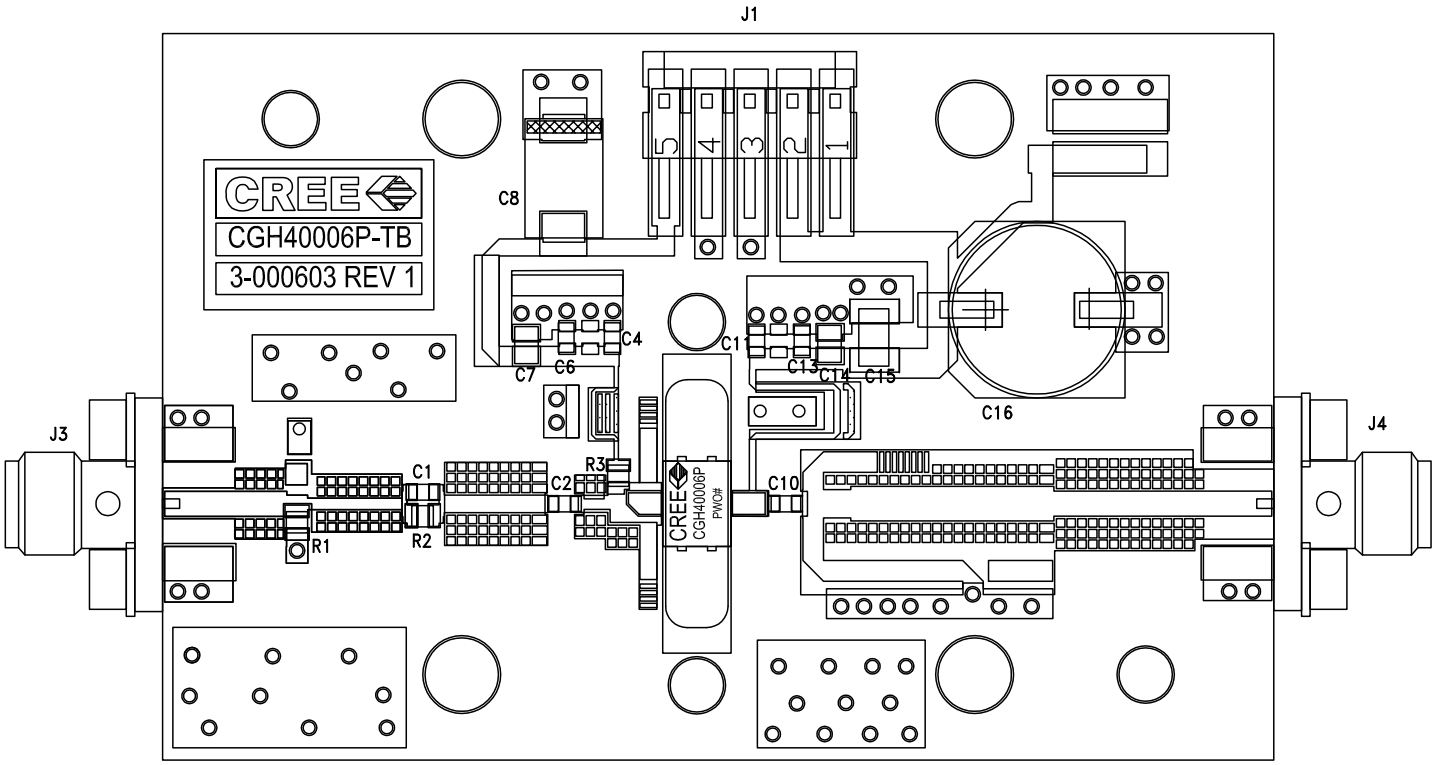


Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

CGH40006P-TB Demonstration Amplifier Circuit Schematic



CGH40006P-TB Demonstration Amplifier Circuit Outline



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

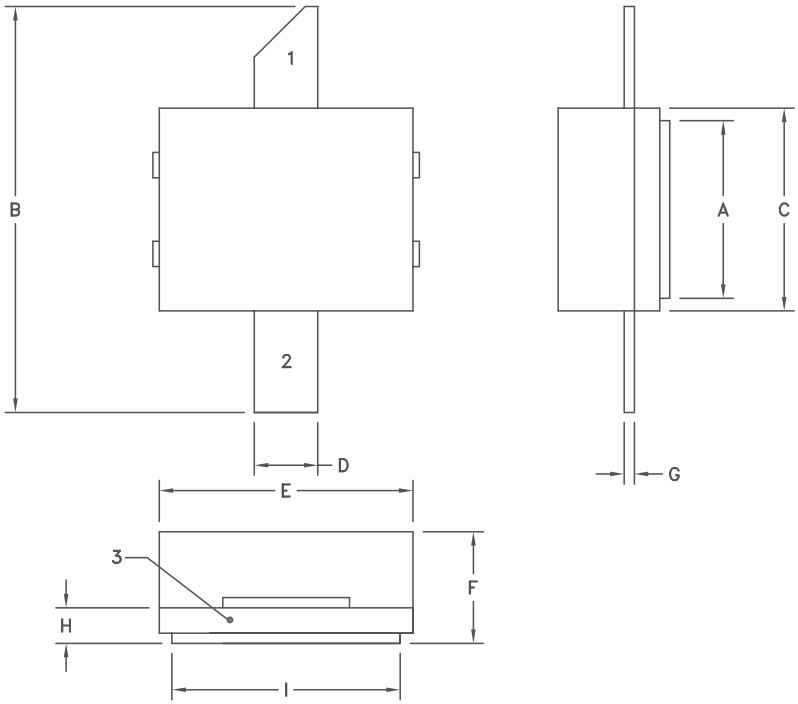
Typical Package S-Parameters for CGH40006P
(Small Signal, V_{DS} = 28 V, I_{DQ} = 100 mA, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.905	-96.56	18.30	120.62	0.023	35.87	0.456	-52.76
600 MHz	0.889	-107.98	16.39	113.31	0.025	29.63	0.429	-58.98
700 MHz	0.877	-117.55	14.76	106.99	0.026	24.39	0.408	-64.31
800 MHz	0.867	-125.66	13.37	101.43	0.027	19.92	0.393	-68.96
900 MHz	0.860	-132.61	12.19	96.46	0.028	16.05	0.381	-73.11
1.0 GHz	0.854	-138.66	11.18	91.94	0.028	12.66	0.374	-76.87
1.1 GHz	0.849	-143.98	10.31	87.79	0.028	9.64	0.368	-80.34
1.2 GHz	0.845	-148.73	9.56	83.92	0.028	6.92	0.366	-83.57
1.3 GHz	0.842	-153.01	8.90	80.29	0.028	4.46	0.365	-86.61
1.4 GHz	0.839	-156.90	8.33	76.84	0.028	2.22	0.365	-89.49
1.5 GHz	0.837	-160.49	7.82	73.56	0.028	0.15	0.367	-92.24
1.6 GHz	0.835	-163.81	7.37	70.40	0.028	-1.75	0.369	-94.88
1.7 GHz	0.833	-166.92	6.96	67.36	0.028	-3.51	0.373	-97.43
1.8 GHz	0.832	-169.85	6.60	64.41	0.028	-5.15	0.376	-99.88
1.9 GHz	0.830	-172.62	6.27	61.54	0.028	-6.67	0.381	-102.27
2.0 GHz	0.829	-175.27	5.98	58.74	0.028	-8.08	0.386	-104.58
2.1 GHz	0.828	-177.81	5.71	56.00	0.028	-9.40	0.391	-106.84
2.2 GHz	0.827	179.75	5.46	53.32	0.027	-10.61	0.396	-109.04
2.3 GHz	0.826	177.38	5.24	50.68	0.027	-11.73	0.401	-111.19
2.4 GHz	0.825	175.07	5.03	48.09	0.027	-12.77	0.407	-113.29
2.5 GHz	0.824	172.82	4.84	45.53	0.027	-13.71	0.412	-115.36
2.6 GHz	0.823	170.61	4.67	43.00	0.026	-14.57	0.418	-117.38
2.7 GHz	0.821	168.44	4.51	40.50	0.026	-15.34	0.423	-119.36
2.8 GHz	0.820	166.30	4.36	38.02	0.026	-16.02	0.428	-121.32
2.9 GHz	0.819	164.18	4.22	35.57	0.026	-16.62	0.434	-123.24
3.0 GHz	0.818	162.08	4.09	33.13	0.026	-17.13	0.439	-125.13
3.2 GHz	0.816	157.91	3.85	28.31	0.025	-17.89	0.449	-128.84
3.4 GHz	0.813	153.76	3.65	23.53	0.025	-18.30	0.458	-132.46
3.6 GHz	0.810	149.58	3.47	18.78	0.025	-18.38	0.467	-136.00
3.8 GHz	0.807	145.35	3.31	14.05	0.024	-18.13	0.474	-139.48
4.0 GHz	0.804	141.05	3.18	9.32	0.024	-17.60	0.481	-142.91
4.2 GHz	0.801	136.66	3.05	4.57	0.024	-16.82	0.488	-146.30
4.4 GHz	0.797	132.15	2.94	-0.20	0.025	-15.89	0.493	-149.67
4.6 GHz	0.793	127.50	2.85	-5.01	0.025	-14.87	0.497	-153.02
4.8 GHz	0.789	122.70	2.76	-9.86	0.026	-13.89	0.500	-156.37
5.0 GHz	0.785	117.72	2.68	-14.79	0.027	-13.04	0.503	-159.74
5.2 GHz	0.780	112.55	2.62	-19.78	0.029	-12.42	0.504	-163.14
5.4 GHz	0.776	107.17	2.55	-24.86	0.030	-12.13	0.505	-166.59
5.6 GHz	0.772	101.58	2.50	-30.03	0.032	-12.22	0.504	-170.10
5.8 GHz	0.768	95.76	2.44	-35.30	0.035	-12.75	0.503	-173.70
6.0 GHz	0.764	89.70	2.40	-40.69	0.037	-13.73	0.501	-177.41

Download this s-parameter file in ".s2p" format at http://www.cree.com/products/wireless_s-parameters.asp

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Product Dimensions CGH40006P (Package Type — 440109)



NOTES: (UNLESS OTHERWISE SPECIFIED)

1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M–1982 DIMENSIONING AND TOLERANCING.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	.135	.145	3.43	3.68
B	.315	.325	8.00	8.26
C	.155	.165	3.94	4.19
D	.045	.055	1.14	1.40
E	.195	.205	4.95	5.21
F	.090	.110	2.29	2.79
G	.007	.009	.178	0.23
H	.026	.030	.660	.762
I	.175	.185	4.45	4.70

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

Disclaimer

Specifications are subject to change without notice. Cree, Inc. believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Cree for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Cree. Cree makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Cree in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Cree products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Cree product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility.

For more information, please contact:

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
www.cree.com/wireless

Sarah Miller
Marketing & Export
Cree, RF Components
1.919.407.5302

Ryan Baker
Marketing
Cree, Wireless Devices
1.919.287.7816

Tom Dekker
Sales Director
Cree, Wireless Devices
1.919.313.5639

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/wireless

LifeElectronics
Живое партнерство

ООО «ЛайфЭлектроникс» **“LifeElectronics” LLC**

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- *Конкурентоспособные цены и скидки постоянным клиентам.*
- *Специальные условия для постоянных клиентов.*
- *Подбор аналогов.*
- *Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.*

- *Приемлемые сроки поставки, возможна ускоренная поставка.*
- *Доставку товара в любую точку России и стран СНГ.*
- *Комплексную поставку.*
- *Работу по проектам и поставку образцов.*
- *Формирование склада под заказчика.*

- *Сертификаты соответствия на поставляемую продукцию (по желанию клиента).*
- *Тестирование поставляемой продукции.*
- *Поставку компонентов, требующих военную и космическую приемку.*
- *Входной контроль качества.*
- *Наличие сертификата ISO.*

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- *Регистрацию проекта у производителя компонентов.*
- *Техническую поддержку проекта.*
- *Защиту от снятия компонента с производства.*
- *Оценку стоимости проекта по компонентам.*
- *Изготовление тестовой платы монтаж и пусконаладочные работы.*

Тел: +7 (812) 336 43 04 (многоканальный)
Email: org@lifeelectronics.ru

www.lifeelectronics.ru